

In the Claims

Claims 1-67 (cancelled).

Claim 68 (previously presented): A semiconductor construction, comprising:

a semiconductive material substrate;

a conductive layer over the substrate, the conductive layer having a thin segment between a pair of thicker segments, one of the thicker segments being a first thicker segment and the other being a second thicker segment;

a first gate stack over the first thicker segment and a second gate stack over the second thicker segment, the first and second gate stacks being spaced from one another by a gap extending over the thin segment;

the first and second gate stacks comprising one or more conductive materials over the thicker segments and comprising one or more insulative materials over the one or more conductive materials; the stacks having sidewalls extending substantially vertically along the thicker segments, one or more conductive materials and one or more insulative materials;

a masking material over portions of the first and second stacks, and having an opening extending therethrough to the thin segment; the opening having a periphery that includes the stack sidewalls; the thicker segments, one or more conductive materials and one or more insulative materials of the stacks being exposed along the stack sidewalls within the opening; and

at least one conductively-doped region within the substrate under the thin segment.

Claim 69 (previously presented): The construction of claim 68 wherein the one or more insulative layers include a layer comprising silicon nitride.

Claim 70 (previously presented): The construction of claim 68 wherein the one or more conductive materials comprise a layer of tungsten over a layer of tungsten nitride.

Claim 71 (previously presented): The construction of claim 68 wherein the thin segment has a thickness of from about 100Å to about 400Å.

Claim 72 (cancelled).

Claim 73 (previously presented): The construction of claim 68 wherein the at least one conductively-doped region includes at least one region which extends to under at least one of the first and second gate stacks.

Claim 74 (previously presented): The construction of claim 68 wherein the conductive layer consists of conductively-doped silicon.

Claim 75 (previously presented): The construction of claim 68 wherein the one or more conductively-doped diffusion regions include at least one conductively-doped diffusion region that extends from one of the gate stacks to the other of the gate stacks.